



08/462742

#4 Phedra B
8/19/95

Docket: 0756-1299

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional PATENT application of)
Hongyong ZHANG et al.)
Based on Serial No. 08/248,220) Art Unit: 2508
Filed: June 5, 1995) Examiner: S. Loke
For: SEMICONDUCTOR DEVICE AND)
FABRICATION METHOD OF THE)
SAME) June 5, 1995

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

Sir:

Please preliminarily amend the subject application as follows:

IN THE CLAIMS

Add new claims 14-25 as follows:

Nub C8
--14. A method for fabricating a semiconductor device, comprising the steps of:

forming a silicon film having an amorphous on a substrate;
preparing a metal element which promotes crystallization before or after formation of the silicon film, to introduce the metal element into an introducing region of the silicon film; and
crystallizing the silicon film,
wherein the silicon film is crystal-grown from the introducing